

## **In the Claims**

Claims 1-70 (cancelled).

Claim 71 (currently amended): A computer system comprising:

a signal source arranged to provide a data signal; and

an inverter coupled with the signal source, configured to invert the data signal and arranged to output the inverted signal; the inverter including:

a structure comprising silicon and germanium;

a first transistor supported by the structure, the first transistor comprising a first gate and a first active region proximate the first gate; the first active region including a first channel region and a pair of first source/drain regions; at least a portion of the first active region being within the structure, the first transistor being a PFET and the first source/drain regions accordingly being p-type doped regions;

an insulative material over at least a portion of the first transistor;

a first layer of semiconductive material over the insulative material  
~~over the first transistor;~~

a second layer of semiconductive material over the first layer, the second layer of semiconductive material ~~formed~~ physically contacting the first layer of semiconductive material, and the second layer of semiconductive material being compositionally different from the first layer of semiconductive material;

a second transistor over the insulative material, and supported by the first and second layers of semiconductive material, the second transistor comprising a second gate and a pair of second source/drain regions, the second transistor being an NFET and the second source/drain regions accordingly being n-type doped regions; the second source/drain regions extending into the second layer of semiconductive material; the second gate being directly over the first gate;

the first and second gates being electrically connected to one another, and being in electrical connection with the signal source; and

one of the first source/drain regions being electrically connected with one of the second source/drain regions and being in electrical connection with the output.

Claim 72 (previously presented): The computer system of claim 71 wherein the second layer of semiconductive material is a crystalline layer having a relaxed crystalline lattice, and further comprising a strained crystalline lattice layer between the second layer of semiconductive material and the second gate.

Claim 73 (original): The computer system of claim 72 wherein the strained crystalline lattice layer includes silicon.

Claims 74 and 75 (canceled).

Claim 76 (original): The computer system of claim 72 wherein the strained crystalline lattice layer includes silicon and germanium.

Claim 77 (canceled).

Claim 78 (original): The computer system of claim 72 wherein the entirety of the relaxed crystalline lattice is a single crystal.

Claim 79 (original): The computer system of claim 72 wherein the relaxed crystalline lattice is polycrystalline.

Claim 80 (original): The computer system of claim 72 wherein the relaxed crystalline lattice includes Si/Ge.

Claim 81 (original): The computer system of claim 80 wherein the relaxed crystalline lattice comprises from about 10 to about 60 atomic percent germanium.

Claims 82-88 (canceled).